Low VcE(sat) Transistor (Strobe flash) (-20V, -10A)

2SA1834

Features

- 1) Low saturation voltage, typically $V_{CE(sat)} = -0.16V$ at $I_C / I_B = -4A / -50mA$.
- High current capacity, typically Ic=-10A for DC operation and -15A for 10ms pulse.
- 3) Complements the 2SC5001.

●Packaging specifications and hre

Ξ	Type	2SA1834
	Package	CPT3
Ξ	hfe	RS
	Code	TL
_	Basic ordering unit (pieces)	2500

●Absolute maximum ratings (Ta=25℃)

•	Parameter	Symbol	Limits	Unit
	Collector-base voltage	Vсво	-30	V
	Collector-emitter voltage	Vceo	-20	V
	Emitter-base voltage	VEBO	-6	V
	Collector current	lc	-10	A
	Collector current	Іср	-15	A *
	Base current	ls .	-2	A
	Collector power dissipation	Pc	1	W
	Collector power dissipation	Po	10	W(Tc=25℃)
	Junction temperature	Tj	150	℃
	Storage temperature	Tstg	-55~+150	℃

^{*} Single pulse Pw=10ms

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Collector-base breakdown voltage	ВУсво	-30	I -	_	V	Ic=-50 μ A	
Collector-emitter breakdown voltage	BVceo	-20	_	_	V	Ic=-1mA	
Emitter-base breakdown voltage	BVEBO	-6	_	_	V	IE=-50 μ A	
Collector cutoff current	Ісво	_	_	-1	μΑ	V _{CB} =-20V	
Emitter cutoff current	Ієво	_	_	-1	μΑ	V _{EB} =-5V	
Collector-emitter saturation voltage	VCE(sat)	_	-0.16	-0.25	V	Ic/Is=-4A/-0.05A	*
Base-emitter saturation voltage	V _{BE(sat)}	_	-0.9	-1.2	V	Ic/I _B =-4A/-0.05A	*
DC	hrei	120	_	560	_	VcE=-2V, Ic=-0.5A	*
DC current transfer ratio	hfE2	82	_	_	_	VcE=-2V , Ic=-4A	*
Transition frequency	fτ	_	150	_	MHz	VcE=-5V , IE=1.5A , f=50MHz	
Output capacitance	Cob	_	220	_	pF	Vcs=-10V, IE=0A, f=1MHz	

^{*} Measured using pulse current.

(96-106-B217)

Low Vce(sat) Transistor (Strobe flash) (20V, 10A)

Features

- 1) Low saturation voltage, typically $V_{\text{CE(sat)}}$ =0.13V at Ic / IB =4A / 50mA.
- 2) High current capacity, typically Ic=10A for DC operation 15A for 10ms pulse.
- 3) Complements the 2SA1834.

●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit	_	
Collector-base voltage	Vсво	30	٧	_	
Collector-emitter voltage	VCEO	Vceo 20			
Emitter-base voltage	VEBO	6	V		
Collector current	lo	10	A		
Collector current	Ice	15	А	*	
Base current	ls	2	Α		
Collector power dissipation	Pc	1	W		
Collector power dissipation	PC	10	W (Tc=25℃)		
Junction temperature	Tj	150	°C		
Storage temperature	Tstg	-55~+150	℃	_	

^{*} Single pulse Pw=10ms

●Packaging specifications and hre

Туре	2SC5001
Package	CPT3
hfE	QR
Code	TL
Basic ordering unit (pieces)	2500

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	ВУсво	30	_	_	V	Ic=50 μ A
Collector-emitter breakdown voltage	BVceo	20	_	_	V	Ic=1mA
Emitter-base breakdown voltage	ВУево	6	_	_	V	IE=50 μ A
Collector cutoff current	Ісво	_	_	1	μΑ	Vcs=20V
Emitter cutoff current	Ієво	_	_	1	μΑ	V _{EB} =5V
Collector-emitter saturation voltage	VCE(sat)	_	0.13	0.25	V	Ic/Is=4A/0.05A
Base-emitter saturation voltage	VBE(sat)	_	_	1.2	V	Ic/I _B =4A/0.05A
DC current transfer ratio	hre1	120	_	390	_	Vce/lc=5V/0.1A
DC current transfer ratio	hre2	82	_	_	_	VcE=2V, Ic=4A
Transition frequency	f⊤	_	150	_	MHz	Vce=5V , le=-1.5A , f=50MHz
Output capacitance	Cob	_	220	_	pF	Vcs=10V, IE=0A, f=1MHz

(96-193-D217)



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